

#### **General Description**

TheWST6225 is the highest performance trench P-ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the small power switching and load switch applications.

The WST6225 meet the RoHS and Green Product requirement, with full function reliability approved.

#### **Features**

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

#### **Product Summery**

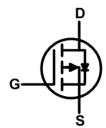
BVDSS	RDSON	ID
-20V	42mΩ	-5.1A

# **Applications**

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

## **SOT-23-3L Pin Configuration**





#### **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units	
$V_{DS}$	Drain-Source Voltage	-20	V	
$V_{GS}$	Gate-Source Voltage	±12	V	
I <sub>D</sub> @T <sub>C</sub> =25℃	Continuous Drain Current, V <sub>GS</sub> @ -4.5V <sup>1</sup>	-5.1	Α	
I <sub>D</sub> @T <sub>C</sub> =70°C	Continuous Drain Current, V <sub>GS</sub> @ -4.5V <sup>1</sup>	-3.9	Α	
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	-15	А	
P <sub>D</sub> @T <sub>A</sub> =25℃	Total Power Dissipation <sup>3</sup>	1	W	
T <sub>STG</sub>	Storage Temperature Range -55 to 150		$^{\circ}$	
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	$^{\circ}$	

#### **Thermal Data**

Symbol	Parameter	Тур.	Max.	Unit
R <sub>0JA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup>		125	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case <sup>1</sup>		80	°C/W



## Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =-250uA	-20			V
$\triangle BV_{DSS}/\triangle T_{J}$	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =-1mA		-0.016		V/°C
		V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-3A		42	55	
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-2.5V , I <sub>D</sub> =-2A		56	70	mΩ
		V <sub>GS</sub> =-1.8V , I <sub>D</sub> =-1A		73	85	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-0.3	-0.5	-1.0	V
$\triangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient			3.97		mV/℃
	Drain-Source Leakage Current	V <sub>DS</sub> =-16V , V <sub>GS</sub> =0V , T <sub>J</sub> =25℃			-1	
I <sub>DSS</sub>		V <sub>DS</sub> =-16V , V <sub>GS</sub> =0V , T <sub>J</sub> =55℃			-5	- uA
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}=\pm 8V$ , $V_{DS}$ =0V			±100	nA
gfs	Forward Transconductance	V <sub>DS</sub> =-5V , I <sub>D</sub> =-3A		14		S
$Q_{g}$	Total Gate Charge (-4.5V)	V <sub>DS</sub> =-15V , V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-3A		12.1	16.9	nC
$Q_gs$	Gate-Source Charge			1.5	2.1	
$Q_gd$	Gate-Drain Charge			3.1	4.3	
$T_{d(on)}$	Turn-On Delay Time			4.4	8.8	
T <sub>r</sub>	Rise Time	V <sub>DD</sub> =-10V , V <sub>GS</sub> =-4.5V ,		45	81	no
T <sub>d(off)</sub>	Turn-Off Delay Time	$R_G=3.3\Omega$ , $I_D=-3A$		48.4	97	ns ns
T <sub>f</sub>	Fall Time			30.4	60.8	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-15V , V <sub>GS</sub> =0V , f=1MHz		938	1313	
C <sub>oss</sub>	Output Capacitance			108	151	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			96	134	

# **Diode Characteristics**

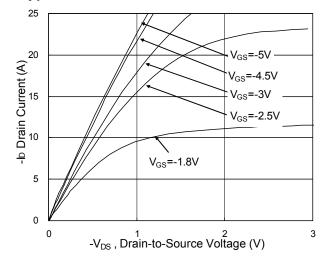
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current <sup>1,4</sup>	V =V =0V Force Current			-4.8	Α
I <sub>SM</sub>	Pulsed Source Current <sup>2,4</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			-15	Α
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}$ =0V , $I_{S}$ =-1A , $T_{J}$ =25 $^{\circ}$ C			-1	V
t <sub>rr</sub>	Reverse Recovery Time			28		nS
Q <sub>rr</sub>	Reverse Recovery Charge	IF=-3A,dI/dt=100A/µs,T <sub>J</sub> =25℃		9		nC

## Note:

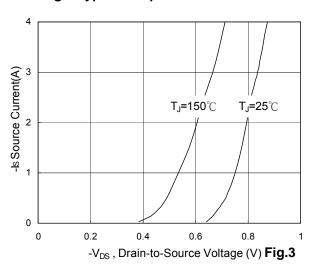
- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq$  300us , duty cycle  $\leq$  2%
- 4.The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.



## **Typical Characteristics**



**Fig.1 Typical Output Characteristics** 



**Forward Characteristics of Reverse** 

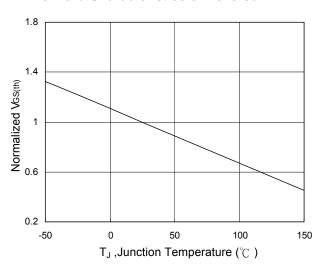


Fig.5 Normalized V<sub>GS(th)</sub> vs. T<sub>J</sub>

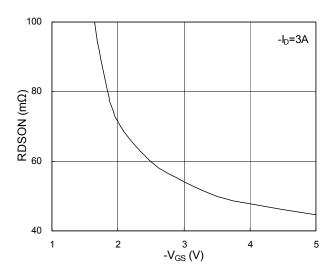


Fig.2 On-Resistance vs. G-S Voltage

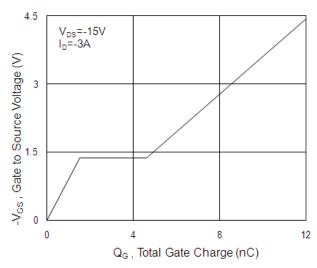


Fig.4 Gate-Charge Characteristics

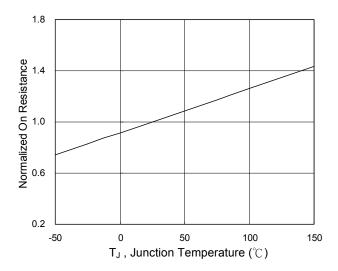
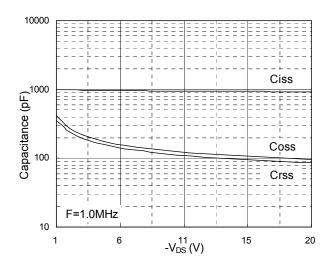


Fig.6 Normalized R<sub>DSON</sub> vs. T<sub>J</sub>





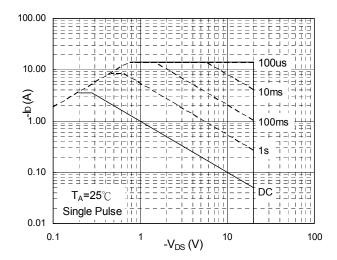


Fig.7 Capacitance

Fig.8 Safe Operating Area

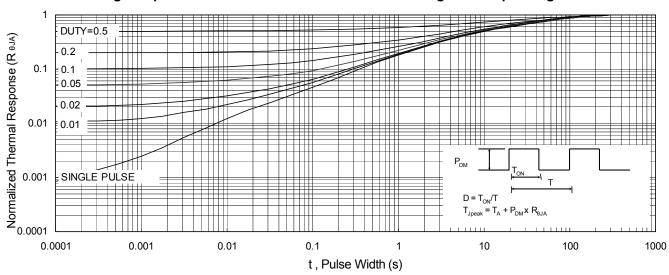
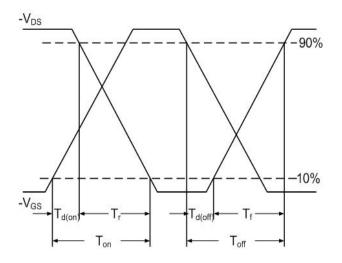


Fig.9 Normalized Maximum Transient Thermal Impedance



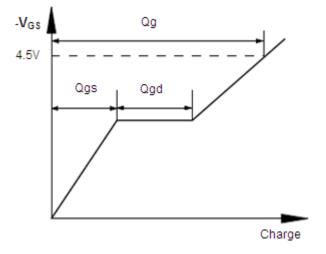


Fig.10 Switching Time Waveform

Fig.11 Gate Charge Waveform



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